

isc Silicon NPN Power Transistors

BUX31/A/B

DESCRIPTION

High Switching Speed

- · Collector-Emitter Sustaining Voltage-
 - : V_{CEO(SUS)}= 400V (Min)-BUX31
 - = 450V (Min)-BUX31A
 - = 500V (Min)-BUX31B
- Low Saturation Voltage
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

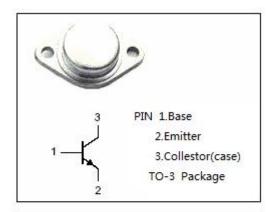
 Designed for off-line power supplies and are also well suited for use in a wide range of inverter or converter circuits and pulse-width-modulated regulators.

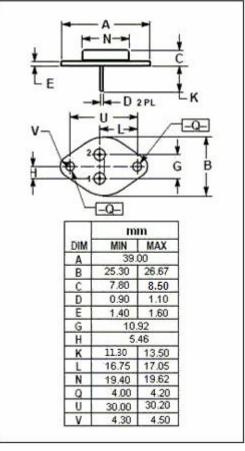
ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

ADSOLUTE MAXIMUM NATINGS(Ta-25 C)						
SYMBOL	PARAMETER		MAX	UNIT		
V _{CES}	Collector- Emitter Voltage(V _{BE} = 0)	BUX31	800	V		
		BUX31A	900			
		BUX31B	1000			
Vceo	Collector-Emitter Voltage	BUX31	400	V		
		BUX31A	450			
		BUX31B	500			
V _{EBO}	Emitter-Base Voltage	8	V			
Ic	Collector Current-Continuous		8	Α		
Ісм	Collector Current-Peak	10	Α			
lΒ	Base Current-Continuou	5	Α			
Pc	Collector Power Dissipation @T _C =25°C		150	W		
Tj	Junction Temperature	200	$^{\circ}\!\mathbb{C}$			
T _{stg}	Storage Temperature Range		-65~200	$^{\circ}$ C		

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R _{th j-c}	Thermal Resistance, Junction to Case	1.0	°C/W







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ELECTRICAL CHARACTERISTICS

Tc=25℃ unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
Vceo(sus)	Collector-Emitter Sustaining Voltage	BUX31	I _C = 50mA ; I _B = 0	400			
		BUX31A		450			V
		BUX31B		500			
V _{CE(sat)-1}	Collector-Emitter Saturation Voltage		I _C = 4A; I _B = 0.8A			1.0	V
V _{CE(sat)-2}	Collector-Emitter Saturation Voltage		I _C = 8A; I _B = 2A			2.0	V
V _{BE(sat)}	Base-Emitter Saturation Voltage		I _C = 4A; I _B = 0.8A			1.3	V
Ісво	Collector Cutoff Current	BUX31	V _{CB} = 800V; I _B = 0 V _{CB} = 800V; I _B = 0,T _C =125°C			0.1 1.0	
		BUX31A	V _{CB} = 900V; I _B = 0 V _{CB} = 900V; I _B = 0,T _C =125°C			0.1 1.0	mA
		BUX31B	V _{CB} = 1000V; I _E = 0 V _{CB} = 1000V; I _E = 0,T _C =125°C			0.1 1.0	
I _{EBO}	Emitter Cutoff Current		V _{EB} = 8V; I _C = 0			2	mA
h _{FE}	DC Current Gain		I _C = 4A ; V _{CE} = 3V	8			

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